2SD1328

Silicon NPN epitaxial planar type

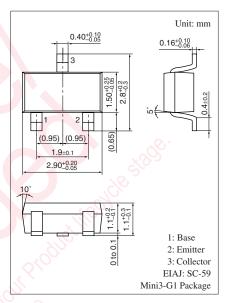
For low-voltage output amplification For muting For DC-DC converter

■ Features

- Low collector-emitter saturation voltage V_{CE(sat)}
- Low ON resistance Ron
- High foward current transfer ratio hFE

■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	25	V
Collector-emitter voltage (Base open)	V _{CEO}	20	V
Emitter-base voltage (Collector open)	V_{EBO}	12	V
Collector current	I_{C}	0.5	A
Peak collector current	I _{CP}	1	A
Collector power dissipation	P _C	200	mW
Junction temperature	T _j	150	°CO
Storage temperature	T_{stg}	-55 to +150	°C
		. 0	7) (0



Marking Symbol: 1D

■ Electrical Characteristics $T_a = 25$ °C ± 3 °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = 10 \mu{\rm A}, I_{\rm E} = 0$	25	0/1/2		V
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = 1 \text{ mA}, I_B = 0$	20	5		V
Emitter-base voltage (Collector open)	$V_{\rm EBO}$	$I_E = 10 \mu\text{A}, I_C = 0$	12			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 25 \text{ V}, I_{E} = 0$	1.1		100	nA
Forward current transfer ratio *1,2	h _{FE}	$V_{CE} = 2 \text{ V}, I_{C} = 0.5 \text{ A}$	200		800	_
Collector-emitter saturation voltage *1	V _{CE(sat)}	$I_C = 0.5 \text{ A}, I_B = 20 \text{ mA}$		0.13	0.40	V
Base-emitter saturation voltage *1	V _{CE(sat)}	$I_C = 0.5 \text{ A}, I_B = 50 \text{ mA}$			1.2	V
Transition frequency	f_T	$V_{CB} = 10 \text{ V}, I_E = -50 \text{ mA}, f = 200 \text{ MHz}$		200		MHz
Collector output capacitance	C _{ob}	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		10		pF
ON resistance *3	R _{ON}	7/6,0 Nr.		1.0		Ω

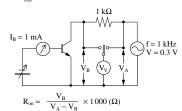
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

- 2. *1: Pulse measurement
 - *2: Rank classification

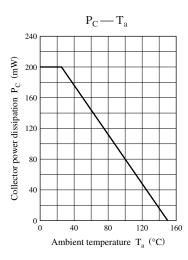
Rank	R	S	Т	No-rank
h_{FE}	200 to 350	300 to 500	400 to 800	200 to 800
Marking symbol	1DR	1DS	1DT	1D

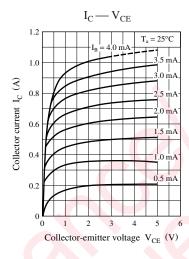
Product of no-rank is not classified and have no marking symbol for rank.

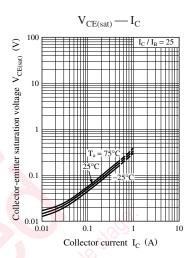
*3: R_{on} Measuremet circuit

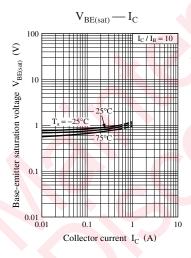


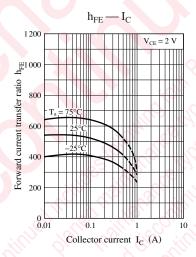
Panasonic

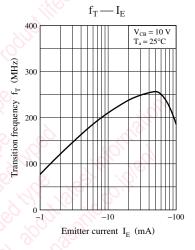


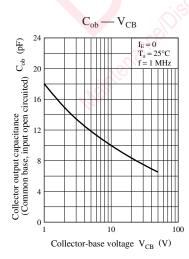












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